

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (L^2 - π -MOSIV)

2SJ315

DC-DC Converter

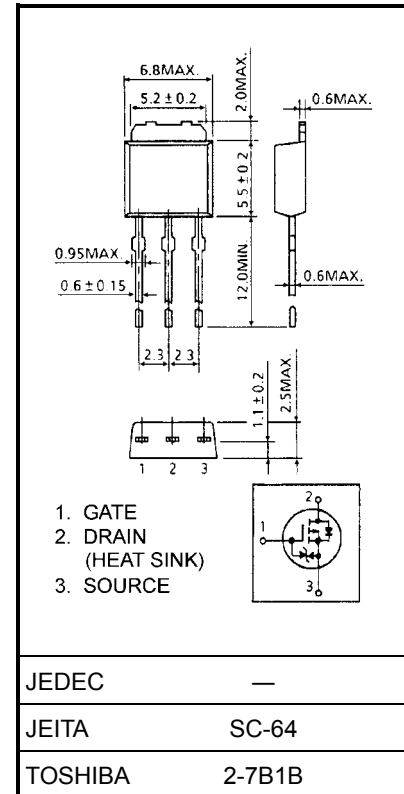
Unit: mm

FEATURES

- 4- Volt gate drive
- Low drain-source ON resistance : $R_{DS(ON)} = 0.25 \Omega$ (typ.)
- High forward transfer admittance : $|Y_{fs}| = 3.0 S$ (typ.)
- Low leakage current : $I_{DSS} = -100 \mu A$ (max) ($V_{DS} = -60 V$)
- Enhancement-mode : $V_{th} = -0.8 \sim -2.0 V$ ($V_{DS} = -10 V$, $I_D = -1 mA$)

Maximum Ratings ($T_a = 25^\circ C$)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	-60	V
Drain-gate voltage ($R_{GS} = 20 k\Omega$)	V_{DGR}	-60	V
Gate-source voltage	V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	A
	Pulse(Note 1)	I_{DP}	
Drain power dissipation ($T_c = 25^\circ C$)	P_D	20	W
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature range	T_{stg}	-55~150	$^\circ C$



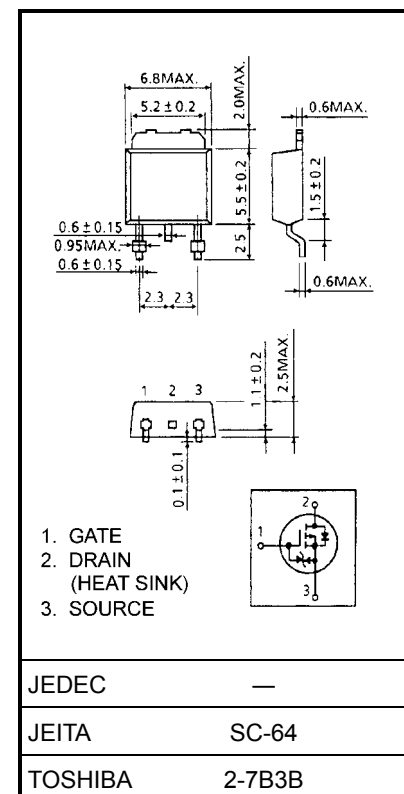
Weight: 0.36 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	6.25	$^\circ C / W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	125	$^\circ C / W$

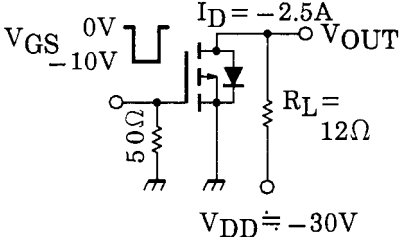
Note 1: Please use devices on condition that the channel temperature is below $150^\circ C$.

This transistor is an electrostatic sensitive device.
Please handle with caution.



Weight: 0.36 g (typ.)

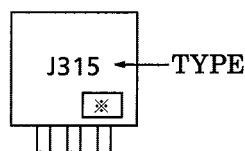
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain cut-off current		I_{DSS}	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-60	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8	—	-2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = -4 \text{ V}, I_D = -2.5 \text{ A}$	—	0.31	0.40	Ω
			$V_{GS} = -10 \text{ V}, I_D = -2.5 \text{ A}$	—	0.21	0.25	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10 \text{ V}, I_D = -2.5 \text{ A}$	1.8	3.0	—	S
Input capacitance		C_{iss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	500	—	pF
Reverse transfer capacitance		C_{rss}		—	90	—	
Output capacitance		C_{oss}		—	290	—	
Switching time	Rise time	t_r	 $V_{GS} = 0 \text{ V}, -10 \text{ V}$ $I_D = -2.5 \text{ A}$ $R_L = 12 \Omega$ $V_{DD} \approx -30 \text{ V}$ $\text{Duty} \leq 1\%, t_w = 10 \mu\text{s}$	—	20	—	ns
	Turn-on time	t_{on}		—	30	—	
	Fall time	t_f		—	30	—	
	Turn-off time	t_{off}		—	140	—	
Total gate charge (Gate-source plus gate-drain)		Q_g	$V_{DD} \approx -48 \text{ V},$ $V_{GS} = -10 \text{ V},$ $I_D = -5 \text{ A}$	—	20	—	nC
Gate-source charge		Q_{gs}		—	13	—	
Gate-drain ("miller") charge		Q_{gd}		—	7	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	-5	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	-20	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = -5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.5	V

Marking



※ Lot Number


 Month (Starting from Alphabet A)


 Year (Last Number of the Christian Era)

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